

# SEMITOP® 2

### **IGBT** Module

#### SK80GM063

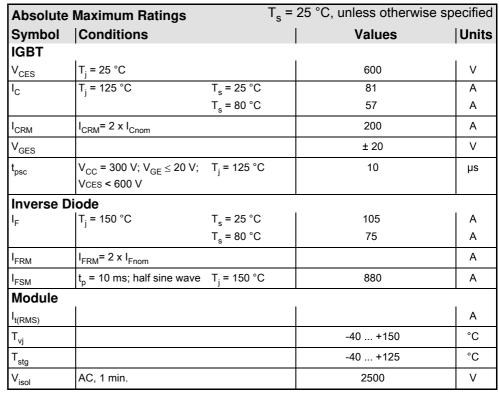
Preliminary Data

#### **Features**

- · Compact design
- · One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- · High short circuit capability
- Low tail current with low temperature dependence

### Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS



Characteristics		$T_s$ = 25 °C, unless otherwise specified						
Symbol	Conditions		min.	typ.	max.	Units		
IGBT								
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 2 \text{ mA}$		4,5	5,5	6,5	V		
I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = V <sub>CES</sub>	T <sub>j</sub> = 25 °C			0,3	mA		
		T <sub>j</sub> = 125 °C				mA		
$I_{GES}$	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = 30 V	T <sub>j</sub> = 25 °C			240	nA		
		T <sub>j</sub> = 125 °C				nA		
$V_{CE0}$		T <sub>j</sub> = 25 °C		0,9		V		
		T <sub>j</sub> = 125 °C		0,9		V		
$r_{CE}$	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 25°C		11		mΩ		
		T <sub>j</sub> = 125°C		15		mΩ		
V <sub>CE(sat)</sub>	I <sub>Cnom</sub> = 100 A, V <sub>GE</sub> = 15 V			2	2,5	V		
		$T_j = 125^{\circ}C_{chiplev.}$		2,4		V		
C <sub>ies</sub>				4,4		nF		
C <sub>oes</sub>	$V_{CE} = 25, V_{GE} = 0 V$	f = 1 MHz				nF		
C <sub>res</sub>				0,4		nF		
$Q_G$	V <sub>GE</sub> =0 20 V			310		nC		
t <sub>d(on)</sub>				45	60	ns		
I t <sub>r</sub>	$R_{Gon}$ = 11 $\Omega$	V <sub>CC</sub> = 300V		35	50	ns		
E <sub>on</sub>	D = 11.0	I <sub>C</sub> = 60A		3 250	300	mJ		
$t_{d(off)} \ t_{f}$	$R_{Goff}$ = 11 $\Omega$	T <sub>j</sub> = 125 °C V <sub>GE</sub> =±15V		250 25	40	ns ns		
E <sub>off</sub>		GE - CO		2,3		mJ		
R <sub>th(j-s)</sub>	per IGBT				0,6	K/W		





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Characteristics									
Symbol	Conditions		min.	typ.	max.	Units			
Inverse Diode									
$V_F = V_{EC}$	$I_{Fnom} = 60 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25  ^{\circ}C_{\text{chiplev.}}$		1,3	1,5	V			
		$T_j = 125  ^{\circ}C_{chiplev.}$		1,2	1,45	V			
$V_{F0}$		T <sub>j</sub> = 125 °C		0,85	0,9	٧			
r <sub>F</sub>		T <sub>j</sub> = 125 °C		5,8	7,5	mΩ			
I <sub>RRM</sub>	I <sub>F</sub> = 60 A	T <sub>i</sub> = 125 °C		22	26	Α			
$Q_{rr}$	di/dt = -500 A/μs	,		2,2	3,5	μC			
E <sub>rr</sub>	V <sub>CC</sub> = 300V			0,2	0,3	mJ			
R <sub>th(j-s)D</sub>	per diode				1,2	K/W			
$M_s$	to heat sink M1				2	Nm			
w				21		g			

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



